BGA2801

MMIC wideband amplifier

Rev. 2 — 29 October 2010

Product data sheet

1. Product profile

1.1 General description

Silicon Monolithic Microwave Integrated Circuit (MMIC) wideband amplifier with internal matching circuit in a 6-pin SOT363 plastic SMD package.

1.2 Features and benefits

- Internally matched to 50 Ω
- A gain of 22.2 dB at 250 MHz increasing to 23.0 dB at 2150 MHz
- Output power at 1 dB gain compression = 2 dBm
- Supply current = 14.3 mA at a supply voltage of 3.3 V
- Reverse isolation > 29 dB up to 2 GHz
- Good linearity with low second order and third order products
- Noise figure = 4 dB at 950 MHz

1.3 Applications

- LNB IF amplifiers
- General purpose low noise wideband amplifier for frequencies between DC and 2.2 GHz

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	V_{CC}		
2, 5	GND2	6 5 4	
3	RF_OUT		6— >—3
4	GND1	0	4 2, 5
6	RF_IN	□1 □2 □3	sym052

3. Ordering information

Table 2. Ordering information

Type number	Package					
	Name	Description	Version			
BGA2801	-	plastic surface-mounted package; 6 leads	SOT363			



MMIC wideband amplifier

4. Marking

Table 3. Marking

	<u> </u>	
Type number	Marking code	Description
BGA2801	*E8	* = - : made in Hong Kong
		* = p : made in Hong Kong
		* = W : made in China
		* = t : made in Malaysia

5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage	RF input AC coupled	-0.5	3.6	V
I _{CC}	supply current		-	55	mΑ
P _{tot}	total power dissipation	T _{sp} = 90 °C	-	200	mW
T _{stg}	storage temperature		-40	+125	°C
Tj	junction temperature		-	125	°C
P _{drive}	drive power		-	-16.5	dBm

6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	$P_{tot} = 200 \text{ mW}; T_{sp} = 90 ^{\circ}\text{C}$	300	K/W

7. Characteristics

Table 6. Characteristics

 $V_{CC} = 3.3 \text{ V; } Z_S = Z_L = 50 \Omega; P_i = -30 \text{ dBm; } T_{amb} = 25 \text{ °C; measured on demo board; unless otherwise specified.}$

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		3.0	3.3	3.6	V
I _{CC}	supply current		12.2	14.3	16.3	mΑ
Gp	power gain	f = 250 MHz	21.6	22.2	22.8	dB
		f = 950 MHz	21.7	22.4	23.1	dB
		f = 2150 MHz	21.5	23.0	24.4	dB
RLin	input return loss	f = 250 MHz	15	17	19	dB
		f = 950 MHz	15	17	19	dB
RL _{in}		f = 2150 MHz	10	12	19	dB
RLout	output return loss	f = 250 MHz	13	17	22	dB
		f = 950 MHz	14	15	16	dB
		f = 2150 MHz	10	12	15	dB
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MMIC wideband amplifier

Table 6. Characteristics ...continued $V_{CC} = 3.3 \text{ V}; Z_S = Z_L = 50 \Omega; P_i = -30 \text{ dBm}; T_{amb} = 25 ^{\circ}\text{C}; measured on demo board; unless otherwise specified.$

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ISL	isolation	f = 250 MHz	58	78	99	dB
		f = 950 MHz	46	47	49	dB
		f = 2150 MHz	29	32	34	dB
NF	noise figure	f = 250 MHz	3.4	3.8	4.3	dB
		f = 950 MHz	3.4	3.8	4.3	dB
		f = 2150 MHz	3.5	3.9	4.4	dB
B _{-3dB}	-3 dB bandwidth	3 dB below gain at 1 GHz	2.5	2.8	3.1	GHz
K	Rollett stability factor	f = 250 MHz	252	308	363	
		f = 950 MHz	7	8	10	
		f = 2150 MHz	0.7	1.3	1.9	
P _{L(sat)}	saturated output power	f = 250 MHz	4	4	5	dBm
		f = 950 MHz	2	4	5	dBm
		f = 2150 MHz	1	2	3	dBm
P _{L(1dB)}	output power at 1 dB gain compression	f = 250 MHz	1	2	3	dBm
		f = 950 MHz	0	2	3	dBm
		f = 2150 MHz	-1	0	1	dBm
IP3 _I	input third-order intercept point	P _{drive} = -34 dBm (for each tone)				
		f ₁ = 250 MHz; f ₂ = 251 MHz	-10	-8	-6	dBm
		f ₁ = 950 MHz; f ₂ = 951 MHz	-11	-8	-6	dBm
		f ₁ = 2150 MHz; f ₂ = 2151 MHz	-17	-14	-10	dBm
IP3 _O	output third-order intercept point	P _{drive} = -34 dBm (for each tone)				
		f ₁ = 250 MHz; f ₂ = 251 MHz	12	14	16	dBm
		f ₁ = 950 MHz; f ₂ = 951 MHz	12	14	16	dBm
		f ₁ = 2150 MHz; f ₂ = 2151 MHz	6	9	13	dBm
P _{L(2H)}	second harmonic output power	P _{drive} = -31 dBm				
		$f_{1H} = 250 \text{ MHz}; f_{2H} = 500 \text{ MHz}$	-62	-60	-58	dBm
		$f_{1H} = 950 \text{ MHz}; f_{2H} = 1900 \text{ MHz}$	-51	-50	-48	dBm
ΔΙΜ2	second-order intermodulation distance	P _{drive} = -34 dBm (for each tone)				
		f ₁ = 250 MHz; f ₂ = 251 MHz	34	45	56	dBc
		f ₁ = 950 MHz; f ₂ = 951 MHz	27	39	50	dBc

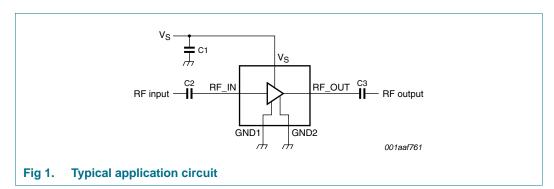
8. Application information

<u>Figure 1</u> shows a typical application circuit for the BGA2801 MMIC. The device is internally matched to $50~\Omega$, and therefore does not need any external matching. The value of the input and output DC blocking capacitors C2 and C3 should not be more than 100 pF for applications above 100 MHz. However, when the device is operated below 100 MHz, the capacitor value should be increased.

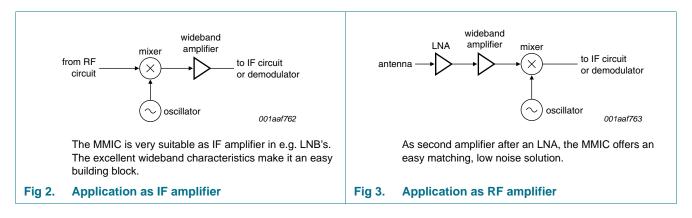
The 22 nF supply decoupling capacitor C1 should be located as close as possible to the MMIC.

MMIC wideband amplifier

The PCB top ground plane, connected to pins 2, 4 and 5 must be as close as possible to the MMIC, preferably also below the MMIC. When using via holes, use multiple via holes as close as possible to the MMIC.



8.1 Application examples



MMIC wideband amplifier

8.2 Graphs

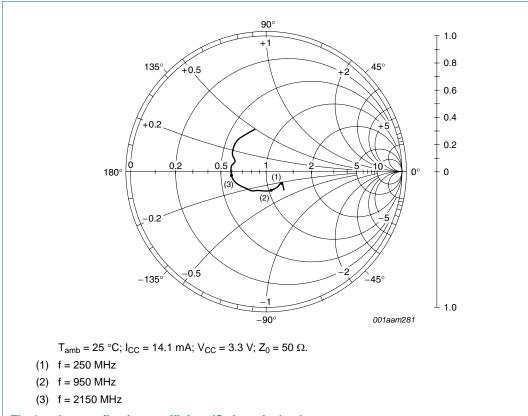
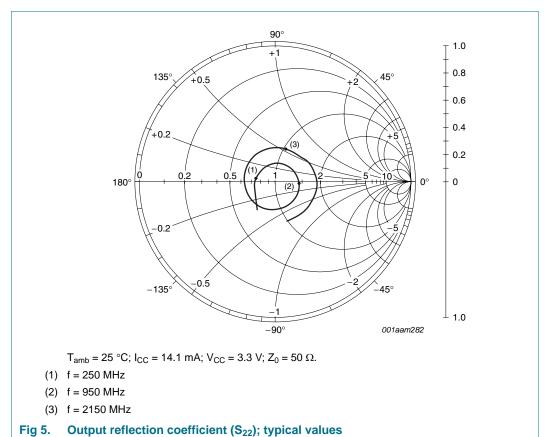
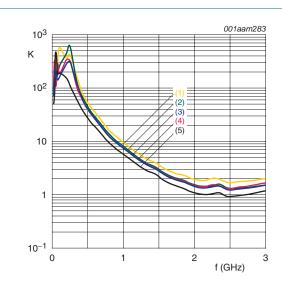


Fig 4. Input reflection coefficient (S₁₁); typical values



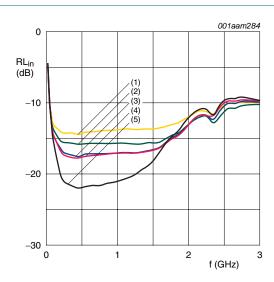
MMIC wideband amplifier



 $P_{drive} = -40 \text{ dBm}$; $Z_0 = 50 \Omega$.

- (1) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 12.52 \,\text{mA}$
- (2) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 12.67 \,\text{mA}$
- (3) $V_{CC} = 3.3 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 14.08 \,\text{mA}$
- (4) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 15.30 \,\text{mA}$
- (5) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.51 \,\text{mA}$

Fig 6. Rollett stability factor as function of frequency; typical values

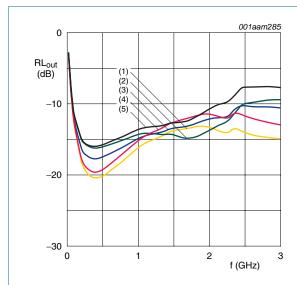


 $P_{drive} = -40 \text{ dBm}; Z_0 = 50 \Omega.$

- (1) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 12.52 \,\text{mA}$
- (2) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 12.67 \,\text{mA}$
- (3) $V_{CC} = 3.3 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 14.08 \,\text{mA}$
- (4) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 15.30 \,\text{mA}$
- (5) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.51 \,\text{mA}$

Fig 7. Input return loss as function of frequency; typical values

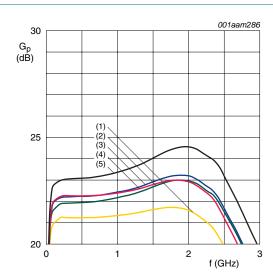
MMIC wideband amplifier



 $P_{drive} = -40 \text{ dBm}$; $Z_0 = 50 \Omega$.

- (1) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 12.52 \,\text{mA}$
- (2) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 12.67 \,\text{mA}$
- (3) $V_{CC} = 3.3 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 14.08 \,\text{mA}$
- (4) $V_{CC} = 3.6 \text{ V}; T_{amb} = 85 \,^{\circ}\text{C}; I_{CC} = 15.30 \text{ mA}$
- (5) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.51 \,\text{mA}$

Fig 8. Output return loss as function of frequency; typical values

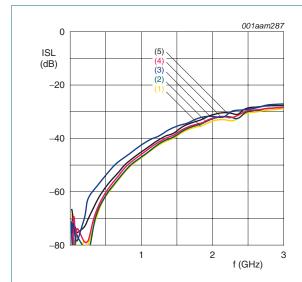


 $P_{drive} = -40 \text{ dBm}; Z_0 = 50 \Omega.$

- (1) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 12.52 \,\text{mA}$
- (2) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 12.67 \,\text{mA}$
- (3) $V_{CC} = 3.3 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 14.08 \,\text{mA}$
- (4) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 15.30 \,\text{mA}$
- (5) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.51 \,\text{mA}$

Fig 9. Insertion power gain as function of frequency; typical values

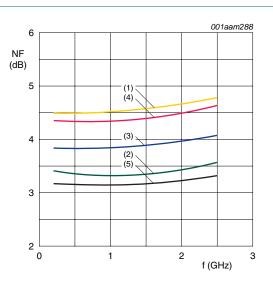
MMIC wideband amplifier



 $P_{drive} = -40 \text{ dBm}$; $Z_0 = 50 \Omega$.

- (1) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 12.52 \,\text{mA}$
- (2) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 12.67 \,\text{mA}$
- (3) $V_{CC} = 3.3 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 14.08 \,\text{mA}$
- (4) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 15.30 \,\text{mA}$
- (5) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.51 \,\text{mA}$

Fig 10. Isolation as function of frequency; typical values



 $Z_0 = 50 \Omega$.

- (1) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 12.52 \,\text{mA}$
- (2) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 12.67 \,\text{mA}$
- (3) $V_{CC} = 3.3 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 14.08 \,\text{mA}$
- (4) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 15.30 \,\text{mA}$
- (5) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.51 \,\text{mA}$

Fig 11. Noise figure as function of frequency; typical values

8.3 Tables

Table 7. Supply current over temperature and supply voltages Typical values.

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	25	85	
I _{CC}	supply current	$V_{CC} = 3.0 \text{ V}$	12.67	12.24	12.52	mA
		$V_{CC} = 3.3 \text{ V}$	14.85	14.08	14.27	mA
		$V_{CC} = 3.6 \text{ V}$	16.51	15.65	15.30	mA

Table 8. Second harmonic output power over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	Tamb	(°C)		Unit
			-40	25	85	
$P_{L(2H)}$	second harmonic output power	$f = 250 \text{ MHz}; P_{drive} = -33 \text{ dBm}$				
		$V_{CC} = 3.0 \text{ V}$	-53	-58	-59	dBm
		$V_{CC} = 3.3 \text{ V}$	-56	-60	-59	dBm
		$V_{CC} = 3.6 \text{ V}$	-58	-60	-59	dBm
		$f = 950 \text{ MHz}; P_{drive} = -33 \text{ dBm}$				
		$V_{CC} = 3.0 \text{ V}$	-46	-50	-54	dBm
		$V_{CC} = 3.3 \text{ V}$	-47	-50	-53	dBm
		$V_{CC} = 3.6 \text{ V}$	-47	-49	-52	dBm

BGA2801

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Table 9. Input power at 1 dB gain compression over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T _{amb} ((°C)		Unit
			-40	25	85	
$P_{i(1dB)} \\$	input power at 1 dB gain compression	f = 250 MHz				
		$V_{CC} = 3.0 \text{ V}$	-20	-20	-20	dBm
	V_{CC} = 3.3 V	-20	-19	-19	dBm	
	$V_{CC} = 3.6 \text{ V}$	-19	-19	-19	dBm	
		f = 950 MHz				
		$V_{CC} = 3.0 \text{ V}$	-20	-20	-20	dBm
		$V_{CC} = 3.3 \text{ V}$	-20	-20	-20	dBm
		$V_{CC} = 3.6 \text{ V}$	-19	-19	-19	dBm
		f = 2150 MHz				
	$V_{CC} = 3.0 \text{ V}$	-22	-22	-22	dBm	
		$V_{CC} = 3.3 \text{ V}$	-21	-21	-22	dBm
		$V_{CC} = 3.6 \text{ V}$	-21	-21	-22	dBm

Table 10. Output power at 1 dB gain compression over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	25	85	
P _{L(1dB)}	output power at 1 dB gain compression	f = 250 MHz		'	'	
		$V_{CC} = 3.0 \text{ V}$	1	1	0	dBm
		$V_{CC} = 3.3 \text{ V}$	2	2	1	dBm
	$V_{CC} = 3.6 \text{ V}$	3	3	2	dBm	
		f = 950 MHz				
		$V_{CC} = 3.0 \text{ V}$	1	0	0	dBm
		$V_{CC} = 3.3 \text{ V}$	2	2	1	dBm
		$V_{CC} = 3.6 \text{ V}$	3	3	2	dBm
		f = 2150 MHz				
		$V_{CC} = 3.0 \text{ V}$	0	-1	-2	dBm
		$V_{CC} = 3.3 \text{ V}$	1	0	-1	dBm
		$V_{CC} = 3.6 \text{ V}$	2	1	0	dBm

Table 11. Saturated output power over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T _{amb}	T _{amb} (°C)		
			-40	25	85	
P _{L(sat)}	saturated output power	f = 250 MHz				
		V _{CC} = 3.0 V	3	3	3	dBm
		$V_{CC} = 3.3 \text{ V}$	4	4	4	dBm
		V _{CC} = 3.6 V	5	5	5	dBm
		f = 950 MHz				
		V _{CC} = 3.0 V	3	3	2	dBm
		$V_{CC} = 3.3 \text{ V}$	4	4	3	dBm
		V _{CC} = 3.6 V	5	5	4	dBm
		f = 2150 MHz				
		V _{CC} = 3.0 V	2	1	0	dBm
		V _{CC} = 3.3 V	3	2	1	dBm
		V _{CC} = 3.6 V	4	3	1	dBm

Table 12. Second-order intermodulation distance over temperature and supply voltages *Typical values.*

Symbol	Parameter	Conditions	T _{amb} (°C)		Unit	
			-40	25	85	
ΔIM2 s	second-order intermodulation distance	$f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$				
		$V_{CC} = 3.0 \text{ V}$	48	48	42	dBc
		$V_{CC} = 3.3 \text{ V}$	52	45	41	dBc
		$V_{CC} = 3.6 \text{ V}$	49	44	41	dBc
		$f_1 = 950 \text{ MHz};$ $f_2 = 951 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$				
		$V_{CC} = 3.0 \text{ V}$	38	38	36	dBc
		$V_{CC} = 3.3 \text{ V}$	40	39	37	dBc
		$V_{CC} = 3.6 \text{ V}$	41	39	37	dBc

Table 13. Output third-order intercept point over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T _{amb}	T _{amb} (°C)		
			-40	25	85	
IP3 _O	output third-order intercept point	$f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$				
		$V_{CC} = 3.0 \text{ V}$	13	13	12	dBm
		$V_{CC} = 3.3 \text{ V}$	15	14	14	dBm
		$V_{CC} = 3.6 \text{ V}$	16	15	14	dBm
		$f_1 = 950 \text{ MHz};$ $f_2 = 951 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$				
		$V_{CC} = 3.0 \text{ V}$	13	12	12	dBm
		$V_{CC} = 3.3 \text{ V}$	15	14	13	dBm
		$V_{CC} = 3.6 \text{ V}$	16	15	14	dBm
		$f_1 = 2150 \text{ MHz};$ $f_2 = 2151 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$				
		$V_{CC} = 3.0 \text{ V}$	9	8	7	dBm
		$V_{CC} = 3.3 \text{ V}$	11	9	8	dBm
		$V_{CC} = 3.6 \text{ V}$	12	10	8	dBm

Table 14. -3 dB bandwidth over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	25	85	
B _{-3dB}	–3 dB bandwidth	$V_{CC} = 3.0 \text{ V}$	2.875	2.832	2.745	GHz
		$V_{CC} = 3.3 \text{ V}$	2.902	2.849	2.763	GHz
		$V_{CC} = 3.6 \text{ V}$	2.920	2.866	2.775	GHz

MMIC wideband amplifier

9. Test information

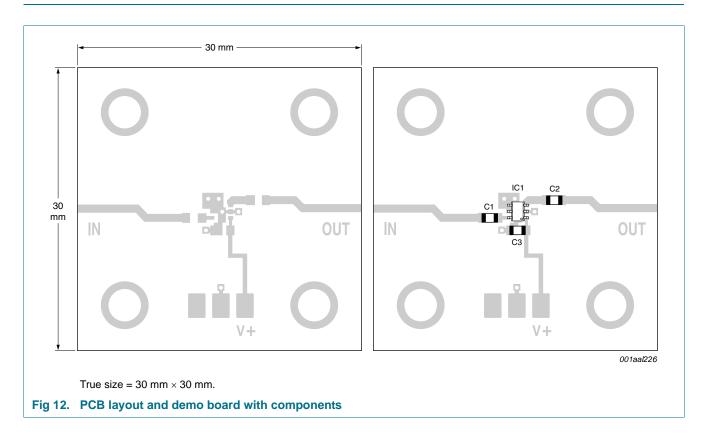


Table 15. List of components used for the typical application

Component	Description	Value	Dimensions
C1, C2	multilayer ceramic chip capacitor	100 pF	0603
C3	multilayer ceramic chip capacitor	22 nF	0603
IC1	BGA2801 MMIC		SOT363

MMIC wideband amplifier

10. Package outline

Plastic surface-mounted package; 6 leads

SOT363

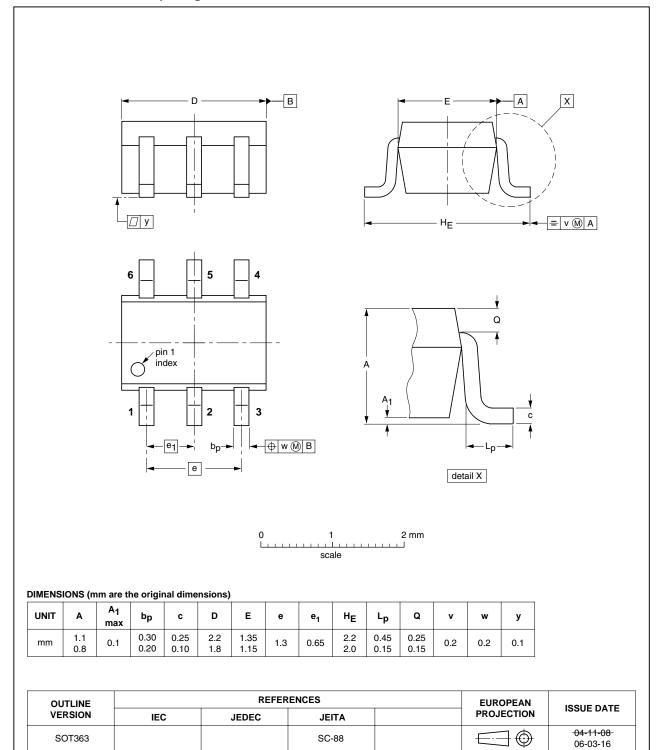


Fig 13. Package outline SOT363

MMIC wideband amplifier

11. Abbreviations

Table 16. Abbreviations

Acronym	Description
DC	Direct Current
IF	Intermediate Frequency
LNA	Low-Noise Amplifier
LNB	Low-Noise Block converter
PCB	Printed-Circuit Board
RF	Radio Frequency
SMD	Surface Mounted Device

12. Revision history

Table 17. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGA2801 v.2	20101029	Product data sheet	-	BGA2801 v.1
Modifications	 Table 4 on page 2: The minimum value for V_{CC} has been changed to −0.5 V 			
BGA2801 v.1	20100817	Product data sheet	-	-

MMIC wideband amplifier

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BGA2801

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BGA2801 NXP Semiconductors

MMIC wideband amplifier

15. Contents

1	Product profile
1.1	General description 1
1.2	Features and benefits
1.3	Applications
2	Pinning information 1
3	Ordering information 1
4	Marking 2
5	Limiting values 2
6	Thermal characteristics 2
7	Characteristics 2
8	Application information 3
8.1	Application examples 4
8.2	Graphs
8.3	Tables
9	Test information
10	Package outline
11	Abbreviations
12	Revision history 15
13	Legal information
13.1	Data sheet status
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks 17
14	Contact information 17
15	Contents 18

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